

FEATURES

33 V supply range 130 Ω on resistance Fully specified at ±15 V/+12 V 3 V logic compatible inputs Rail-to-rail operation Break-before-make switching action 20-lead SSOP

APPLICATIONS

Audio and video routing Battery-powered systems Signal routing

GENERAL DESCRIPTION

The ADG1334 is a monolithic CMOS device comprising four independently selectable SPDT switches designed on a CMOS process.

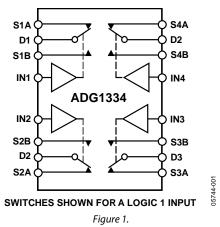
When the switches are on, each switch conducts equally well in both directions and has an input signal range that extends to the power supplies. In the off condition, signal levels up to the supplies are blocked. All switches exhibit break-before-make switching action for use in multiplexer applications. Inherent in the design is the low charge injection for minimum transients when switching the digital inputs.

Fast switching speed coupled with high signal bandwidth makes the part suitable for video signal switching. CMOS construction ensures ultra ow power dissipation, making the part ideally suited for portable and battery-powered instruments.

Quad SPDT ±15 V/+12 V Switches

ADG1334

FUNCTIONAL BLOCK DIAGRAM



PRODUCT HIGHLIGHTS

- 1. 3 V logic compatible digital input V_{IH} = 2.0 V, V_{IL} = 0.8 V.
- 2. No V_L logic power supply required.
- 3. Low power consumption.
- 4. 20-lead SSOP.

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ADG1334* Product Page Quick Links

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Comparable Parts

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Evaluation Kits

• Evaluation Board for 24-Lead TSSOP Devices in the Switches and Multiplexers Portfolio

Documentation 🖵

Data Sheet

• ADG1334: Quad SPDT $\pm 15 \text{ V/}+12 \text{ V}$ Switches Data Sheet

User Guides

• UG-1036: Evaluation Board for 24-Lead TSSOP Devices in the Switches and Multiplexers Portfolio

Reference Materials

Product Selection Guide

• Switches and Multiplexers Product Selection Guide

Design Resources 🖵

- ADG1334 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- · Symbols and Footprints

Discussions 🖵

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Sample and Buy

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REVISION HISTORY

1/06—Revision 0: Initial Version

SPECIFICATIONS

DUAL SUPPLY¹

 V_{DD} = +15 V \pm 10%, V_{SS} = –15 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

	В	B Version			
Parameter	+25°C	−40°C to +105°C	Unit	Test Conditions/Comments	
ANALOG SWITCH	+25 C	+105 C	Onic	Test conditions/comments	
Analog Signal Range		V _{ss} to V _{DD}	v		
On Resistance (R_{ON})	130	230	Ω typ	$V_{s} = \pm 10 V$, $I_{s} = -10 mA$; see Figure 11	
	200	230	Ωmax	$V_{DD} = +13.5 \text{ V}, V_{SS} = -13.5 \text{ V}$	
On Resistance Match Between Channels (ΔR_{ON})	5		Ωtyp	$V_{s} = \pm 10 \text{ V}, \text{ I}_{s} = -10 \text{ mA}$	
of hesistance match between channels (Bhon)	10		$\Omega \max$		
On Resistance Flatness (R _{FLAT (ON)})	25		Ωtyp	$V_s = -5 V_r 0 V_r + 5 V_r I_s = -10 \text{ mA}$	
	65		Ωmax		
LEAKAGE CURRENTS	0.5		11 1100	$V_{DD} = +16.5 \text{ V}, \text{ V}_{SS} = -16.5 \text{ V}$	
Source Off Leakage Is (Off)	±10		nA typ	$V_D = \pm 10 \text{ V}; \text{ V}_S = \pm 10 \text{ V}; \text{ see Figure 12}$	
Drain Off Leakage I _D (Off)	±10		nA typ	$V_D = \pm 10 \text{ V}; V_S = \pm 10 \text{ V}; \text{ see Figure 12}$	
Channel On Leakage I _D , I _s (On)	±10		nA typ	$V_{s} = V_{D} = \pm 10 \text{ V}$; see Figure 13	
DIGITAL INPUTS	_10		1		
Input High Voltage, VINH		2.0	V min		
Input Low Voltage, V _{INL}		0.8	V max		
	±0.005	010	μA typ	VIN = VINI OF VINH	
	_0.000	±0.1	µA max		
Digital Input Capacitance, C _{IN}	5		pF typ		
DYNAMIC CHARACTERISTICS ²			P: 7F		
Ton	110		ns typ	$R_L = 300 \Omega, C_L = 35 pF$	
	130	150	ns max	$V_s = 10 V$; see Figure 14	
T _{OFF}	65		ns typ	$R_L = 300 \Omega, C_L = 35 pF$	
	85	95	ns max	$V_s = 10 V$; see Figure 14	
Тввм	25		ns typ	$R_L = 300 \Omega, C_L = 35 pF$	
		10	ns min	$V_{s1} = V_{s2} = +10 V$; see Figure 15	
Charge Injection	2		pC typ	$V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 16	
Off Isolation	80		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 17	
Channel-to-Channel Crosstalk	85		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 19	
–3 dB Bandwidth	700		MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 18	
Cs (Off)	5		pF typ	$f = 1 MHz; V_s = 0 V$	
C_{D} (Off)	5		pF typ	$f = 1 MHz; V_s = 0 V$	
C _D , C _s (On)	10		pF typ	$f = 1 MHz; V_s = 0 V$	
POWER REQUIREMENTS				$V_{DD} = +16.5 V, V_{SS} = -16.5 V$	
l _{DD}	0.002		μA typ	Digital inputs = $0 V$ or V_{DD}	
		1	µA max		
lod	260		μA typ	Digital inputs = 5 V	
		400	µA max		
lss	0.002		μA typ	Digital inputs = $0 V \text{ or } V_{DD}$	
		1	µA max		
lss	0.002		μA typ	Digital inputs = 5 V	
		1	µA max		

¹ Temperature range is B Version: -40°C to +105°C. ² Guaranteed by design, not subject to production test.

SINGLE SUPPLY¹

 V_{DD} = 12 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

	B Version				
Parameter	+25°C	–40°C to +105°C	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		0 to V_{DD}	V		
On Resistance (R _{ON})	325	520	Ωtyp	$V_s = 0 V to 10 V$, $I_s = -10 mA$; see Figure 11	
	500		Ωmax	$V_{DD} = 10.8 V, V_{SS} = 0 V$	
On Resistance Match Between Channels (ΔR_{ON})	10		Ωtyp	$V_s = 0 V to 10 V, I_s = -10 mA$	
	20		Ωmax		
On Resistance Flatness (R _{FLAT(ON)})	65		Ωtyp	$V_s = 3 V, 6 V, 9 V, I_s = -10 mA$	
LEAKAGE CURRENTS				V _{DD} = 13.2 V	
Source Off Leakage Is (Off)	±10		nA typ	$V_s = 1 V/10 V$, $V_D = 10 V/1 V$; see Figure 12	
Drain Off Leakage I₀ (Off)	±10		nA typ	$V_s = 1 \text{ V}/10 \text{ V}, V_D = 10 \text{ V}/1 \text{ V}; \text{ see Figure 12}$	
Channel On Leakage I _D , I _s (On)	±10		nA typ	$V_s = V_D = 1 V \text{ or } 10 V$, see Figure 13	
DIGITAL INPUTS					
Input High Voltage, VINH		2.0	V min		
Input Low Voltage, V _{INL}		0.8	V max		
Input Current, I _{INL} or I _{INH}	±0.005		μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$	
		±0.1	µA max		
Digital Input Capacitance, C _{IN}	3		pF typ	f = 1 MHz	
DYNAMIC CHARACTERISTICS ²					
T _{ON}	135		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$	
	170	200	ns max	$V_s = 8 V$; see Figure 14	
Toff	95		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$	
	115	140	ns max	$V_s = 8 V$; see Figure 14	
Тввм	50		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$	
		10	ns min	$V_{s1} = V_{s2} = 8 V$; see Figure 15	
Charge Injection	2		pC typ	$V_s = 6 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 16	
Off Isolation	80		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 17	
Channel-to-Channel Crosstalk	85		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 19	
–3 dB Bandwidth	500		MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 18	
Cs (Off)	5		pF typ	$f = 1 MHz; V_s = 6 V$	
C _D (Off)	5		pF typ	$f = 1 MHz; V_s = 6 V$	
C _D , C _s (On)	10		pF typ	$f = 1 MHz; V_s = 6 V$	
POWER REQUIREMENTS				V _{DD} = 13.2 V	
l _{DD}	0.002		μA typ	Digital inputs = $0 V \text{ or } V_{DD}$	
		1	μA max		
lod	260		µA typ	Digital inputs = 5 V	
		420	μA max		

 1 Temperature range is B Version: –40°C to +105°C. 2 Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 3.

Parameter	Rating
V _{DD} to V _{SS}	35 V
V _{DD} to GND	–0.3 V to +25 V
Vss to GND	+0.3 V to -25 V
Analog, Digital Inputs ¹	V _{ss} – 0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first
Continuous Current, S or D	24 mA
Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle max)	100 mA
Operating Temperature Range	
Industrial Temperature Range (B Version)	–40°C to +105°C
Storage Temperature Range	–65°C to +150°C
Junction Temperature	150°C
SSOP Package	
$ heta_{JA}$, Thermal Impedance	83.2°C/W
Reflow Soldering Peak Temperature, Pb-free	260°C

¹ Overvoltages at A, EN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

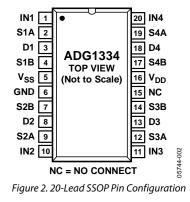


Table 4. 20-Lead SSOP Pin Function Descriptions

Pin No.	Mnemonic	Description		
1, 10, 11, 20	IN1, IN2, IN3, IN4	Logic Control Input.		
2, 4, 7, 9, 12, 14, 17, 19	S1A, S1B, S2B, S2A, S3A, S3B, S4B, S4A	Source Terminal. Can be an input or output.		
3, 8, 13, 18	D1, D2, D3, D4	Drain Terminal. Can be an input or output.		
5	Vss	Most Negative Power Supply Potential in Dual Supplies. In single-supply applications, it can be connected to ground.		
6	GND	Ground (0 V) Reference.		
15	NC	No Connect.		
16	V _{DD}	Most Positive Power Supply Potential.		

Table 5. ADG1334 Truth Table

Logic	Switch A	Switch B
0	Off	On
1	On	Off

TERMINOLOGY

R_{ON} Ohmic resistance between D and S.

 ΔR_{ON} Difference between the R_{ON} of any two channels.

Is (Off) Source leakage current when switch is off.

I_D (Off) Drain leakage current when switch is off.

I_D, I_s (On) Channel leakage current when switch is on.

V_D (V_S) Analog voltage on Terminal D, Terminal S.

Cs (OFF) Channel input capacitance for off condition.

 C_D (Off) Channel output capacitance for off condition.

C_D, Cs (On) On switch capacitance.

C_{IN} Digital input capacitance.

ton

The delay between applying the digital control input and the output switching on (see Figure 14).

toff

The delay between applying the digital control input and the output switching off (see Figure 14).

tввм Off time measured between the 80% point of both switches when switching from one address state to another.

 \mathbf{V}_{INL} Maximum input voltage for Logic 0.

 \mathbf{V}_{INH} Minimum input voltage for Logic 1.

I_{INL} (I_{INH}) Input current of the digital input.

IDD Positive supply current.

Iss Negative supply current.

Off Isolation A measure of unwanted signal coupling through an off channel.

Charge Injection A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Bandwidth Frequency at which the output is attenuated by 3 dB.

On Response Frequency response of the on switch.

TYPICAL PERFORMANCE CHARACTERISTICS

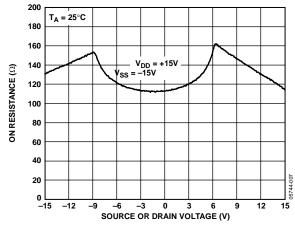


Figure 3. On Resistance as a Function of $V_D(V_S)$ for Dual Supply

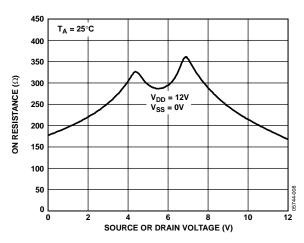


Figure 4. On Resistance as a Function of $V_D(V_S)$ for Single Supply

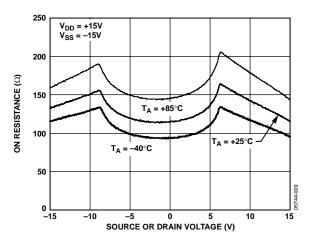


Figure 5. On Resistance as a Function of V_D (V_S) for Different Temperatures, Dual Supply

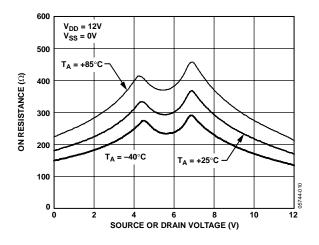


Figure 6. On Resistance as a Function of V_D (V_S) for Different Temperatures, Single Supply

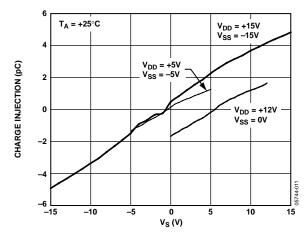


Figure 7. Charge Injection vs. Source Voltage

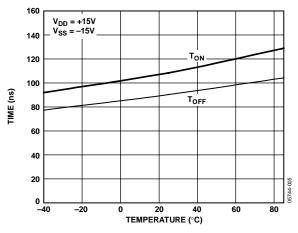
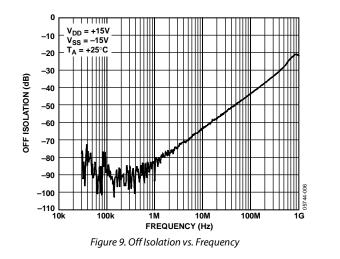
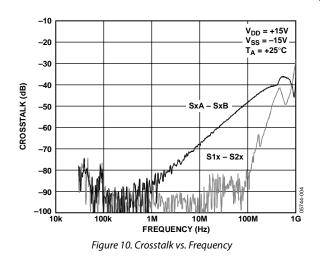
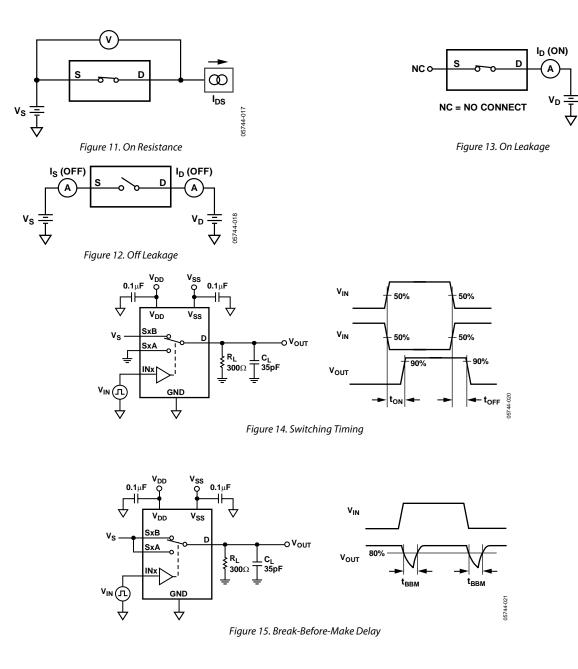


Figure 8. T_{ON}/T_{OFF} Time vs. Temperature

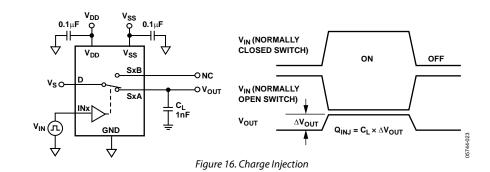


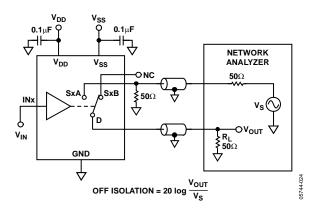


TEST CIRCUITS



05744-019





v_{ss} Q **0.1**μ**F** 0.1 ┉ 신 NETWORK ANALYZER V_{SS} V_{DD} SxA V_{OUT} O- **50**Ω **50**Ω c ₹ } **8** 50Ω ∇ SxB D E) € INxO GND Å 05744-026 $rac{v_{out}}{v_s}$ CHANNEL-TO-CHANNEL CROSSTALK = 20 log

VDD

Figure 19. Channel-to-Channel Crosstalk

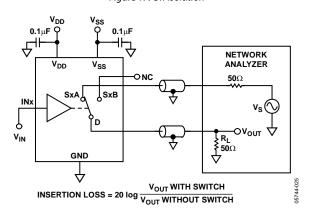
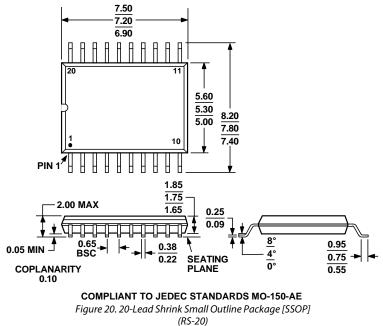


Figure 17. Off Isolation

Figure 18. Bandwidth

OUTLINE DIMENSIONS



Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Description	Package Option
ADG1334BRSZ ¹	-40°C to +105°C	20-Lead Shrink Small Outline Package (SSOP)	RS-20
ADG1334BRSZ-REEL ¹	-40°C to +105°C	20-Lead Shrink Small Outline Package (SSOP)	RS-20

 1 Z = Pb-free part.

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